

Silicon NPN Power Transistors 2SD1274 2SD1274A 2SD1274B

DESCRIPTION

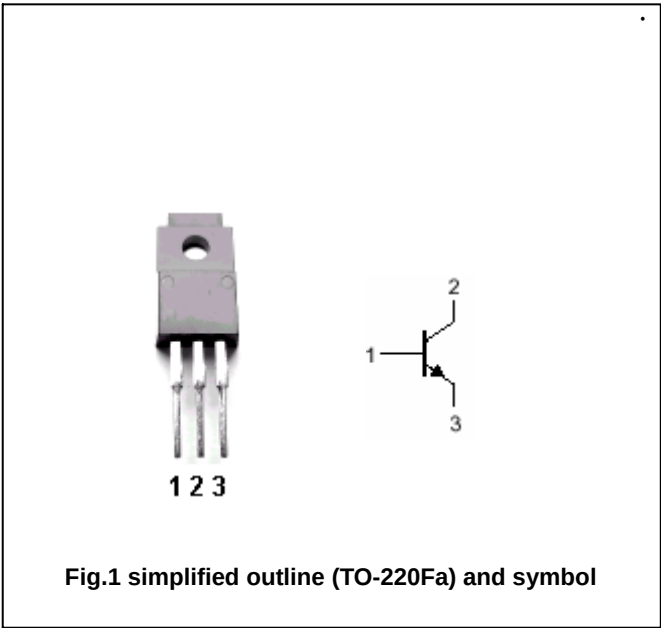
- With TO-220Fa package
- High V_{CBO}
- High speed switching

APPLICATIONS

- Power amplifier applicaitons

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD1274	150	V
		2SD1274A	200	
		2SD1274B	250	
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		5	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	40	W
		$T_a=25^{\circ}\text{C}$	2	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

Silicon NPN Power Transistors**2SD1274 2SD1274A 2SD1274B****CHARACTERISTICS**

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage		$I_C=0.2A$, $L=25mH$	80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E=1mA$, $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=5A$; $I_B=1A$			1.6	V
V_{BE}	Base-emitter voltage		$I_C=5A$; $V_{CE}=4V$			1.5	V
I_{CBO}	Collector cut-off current	2SD1274	$V_{CB}=150V$; $I_E=0$			1	mA
		2SD1274A	$V_{CB}=200V$; $I_E=0$				
		2SD1274B	$V_{CB}=250V$; $I_E=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=5V$; $I_C=0$			50	μA
h_{FE}	DC current gain		$I_C=5A$; $V_{CE}=4V$	14			
f_T	Transition frequency		$I_C=0.5A$; $V_{CE}=10V$		40		MHz
t_f	Fall time		$I_C=5A$; $I_{B1}=0.8A$ $V_{EB}=-5V$			1.0	μs

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PACKAGE OUTLINE

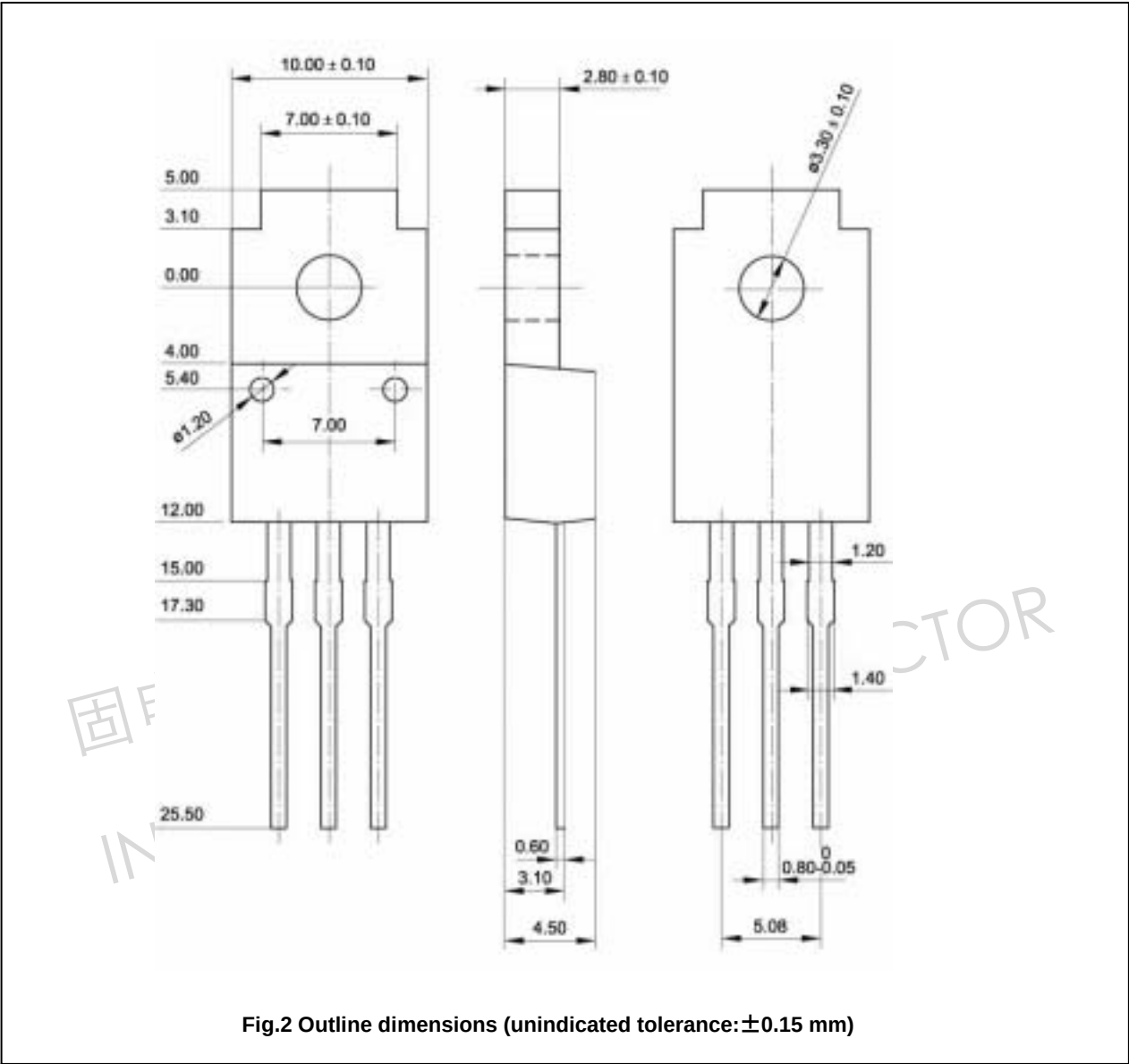


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)